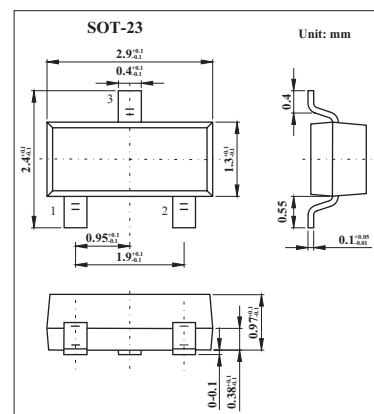


Silicon Epitaxial Schottky Barrier Diode

1SS345

■ Features

- Small interterminal capacitance ($C=0.45\text{pF}$ typ).
- Low forward voltage and excellent detection efficiency ($V_F=0.35\text{V}$ max)
- High breakdown voltage ($V_R=55\text{V}$).
- Very small-sized package permitting the 1SS345-applied sets to be made small and slim.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	55	V
Forward Current	I_F	10	mA
Power Dissipation	P	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$
Reverse Burning	$C = 25 \text{ pF}$ B_o	2	erg

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 1 \text{ mA}$			0.35	V
Forward Current	I_F	$V_F = 1 \text{ V}$	10			mA
Reverse Voltage	V_R	$I_R = 100 \mu\text{A}$	55			V
Reverse Current	I_R	$V_R = 40 \text{ V}$			50	μA
Interterminal Capacitance	C	$V_R = 10 \text{ V}, f = 1 \text{ MHz}$		0.45		pF

■ Marking

Marking	AH
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